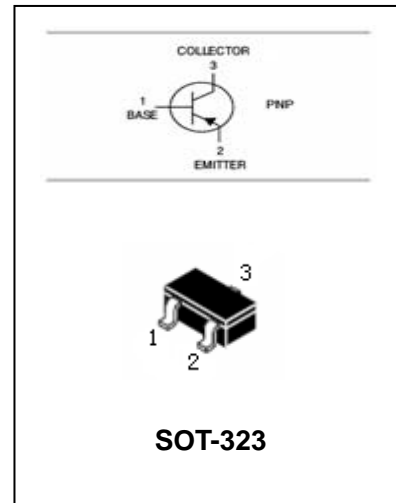


## PNP General Purpose Transistor

## MMST5401

### FEATURES

- Epitaxial planar die construction.
- Complementary NPN type available (MMST5551).
- Also available in lead free version.



### APPLICATIONS

- Ideal for medium power amplification and switching.

### ORDERING INFORMATION

| Type No. | Marking | Package Code |
|----------|---------|--------------|
| MMST5401 | K4M     | SOT-323      |

### MAXIMUM RATING @ Ta=25°C unless otherwise specified

| Symbol                            | Parameter                              | Value   | UNIT |
|-----------------------------------|--|---------|------|
| V <sub>CBO</sub>                  | collector-base voltage                 | -160    | V    |
| V <sub>CEO</sub>                  | collector-emitter voltage              | -150    | V    |
| V <sub>EBO</sub>                  | emitter-base voltage                   | -5      | V    |
| I <sub>C</sub>                    | collector current (DC)                 | -0.6    | A    |
| P <sub>C</sub>                    | Collector dissipation                  | 0.2     | W    |
| R <sub>θJA</sub>                  | Thermal resistance junction to ambient | 625     | °C/W |
| T <sub>J</sub> , T <sub>stg</sub> | junction and storage temperature       | -55-150 | °C   |

### ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

## PNP General Purpose Transistor

## MMST5401

| Symbol        | Parameter                            | Test conditions  | MIN.           | MAX.          | UNIT |
|---------------|--------------------------------------|--|----------------|---------------|------|
| $V_{(BR)CBO}$ | Collector-base breakdown voltage     | $I_C = -100\mu A, I_E = 0$   | -160           |               |      |
| $V_{(BR)CEO}$ | Collector-emitter breakdown voltage  | $I_C = -1mA, I_B = 0$  | -150           |               |      |
| $V_{(BR)EBO}$ | Emitter-base breakdown voltage       | $I_E = -10\mu A, I_C = 0$  | -5             |               |      |
| $I_{CBO}$     | collector cut-off current            | $I_E = 0; V_{CB} = -120V$  | -              | -50           | nA   |
| $I_{EBO}$     | emitter cut-off current              | $I_C = 0; V_{EB} = -3V$  | -              | -50           | nA   |
| $h_{FE}$      | DC current gain                      | $V_{CE} = -5V; I_C = -1mA$<br>$V_{CE} = -5V; I_C = -10mA$<br>$V_{CE} = -5V; I_C = -50mA$ | 50<br>60<br>50 | -<br>240<br>- |      |
| $V_{CE(sat)}$ | collector-emitter saturation voltage | $I_C = -50mA; I_B = -5mA$<br>$I_C = -10mA; I_B = -1mA$                                   | -              | -0.5<br>-0.2  | V    |
| $V_{BE(sat)}$ | base-emitter saturation voltage      | $I_C = -50mA; I_B = -5mA$<br>$I_C = -10mA; I_B = -1mA$                                   | -              | -1<br>-1      | V    |
| $f_T$         | transition frequency                 | $I_C = -10mA; V_{CE} = -10V,$<br>$f = 100MHz$  | 100            | 300           | MHz  |
| NF            | Noise figure                         | $I_C = -200mA, V_{CE} = -5.0V,$<br>$f = 100MHz$  |                | 8             | dB   |

### TYPICAL CHARACTERISTICS @ $T_a = 25^\circ C$ unless otherwise specified

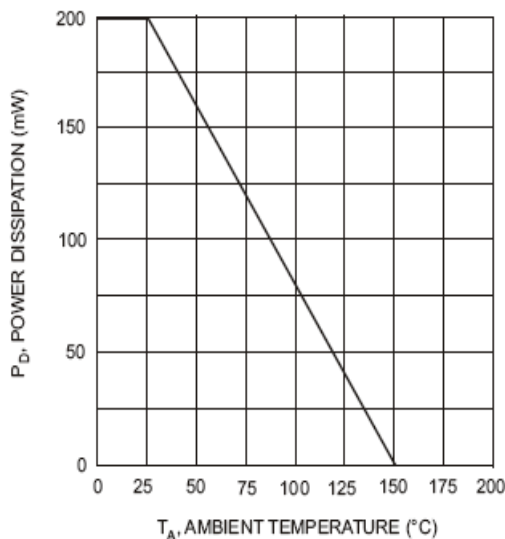


Fig. 1, Max Power Dissipation vs Ambient Temperature

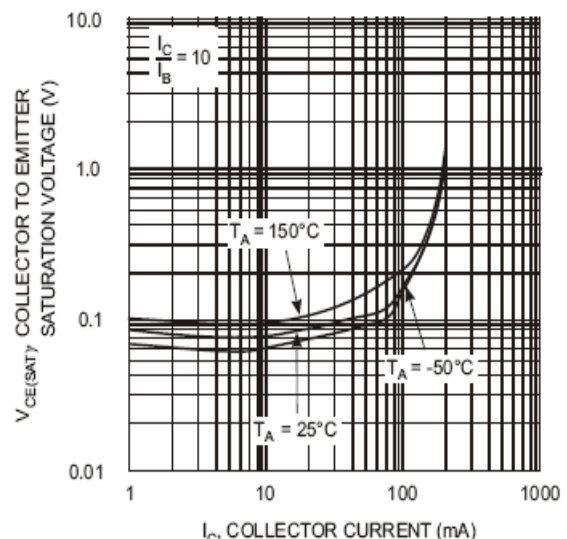


Fig. 2, Collector Emitter Saturation Voltage vs. Collector Current

**PNP General Purpose Transistor**

**MMST5401**

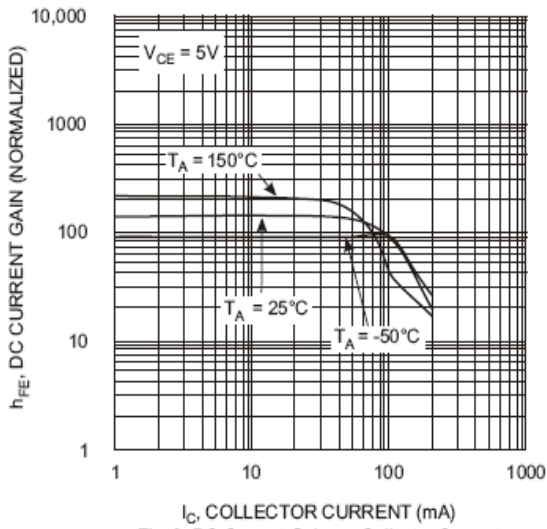


Fig. 3, DC Current Gain vs. Collector Current

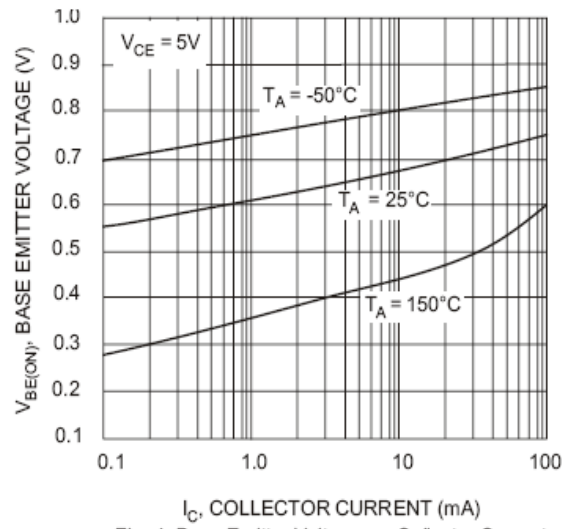


Fig. 4, Base Emitter Voltage vs. Collector Current

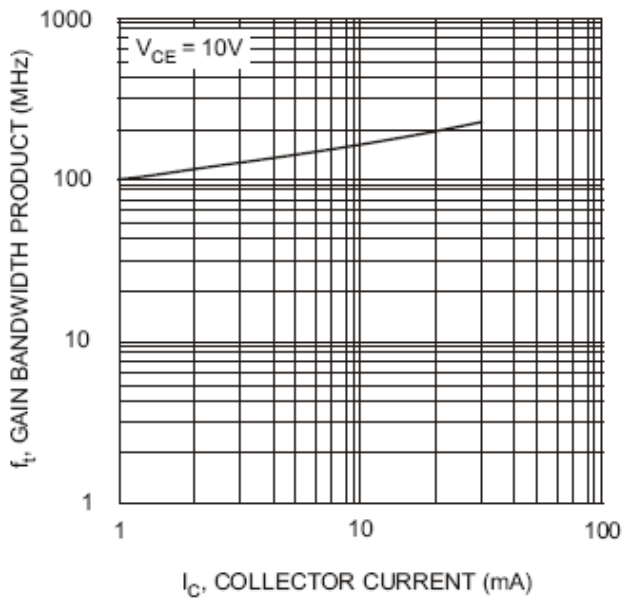


Fig. 5, Gain Bandwidth Product vs Collector Current

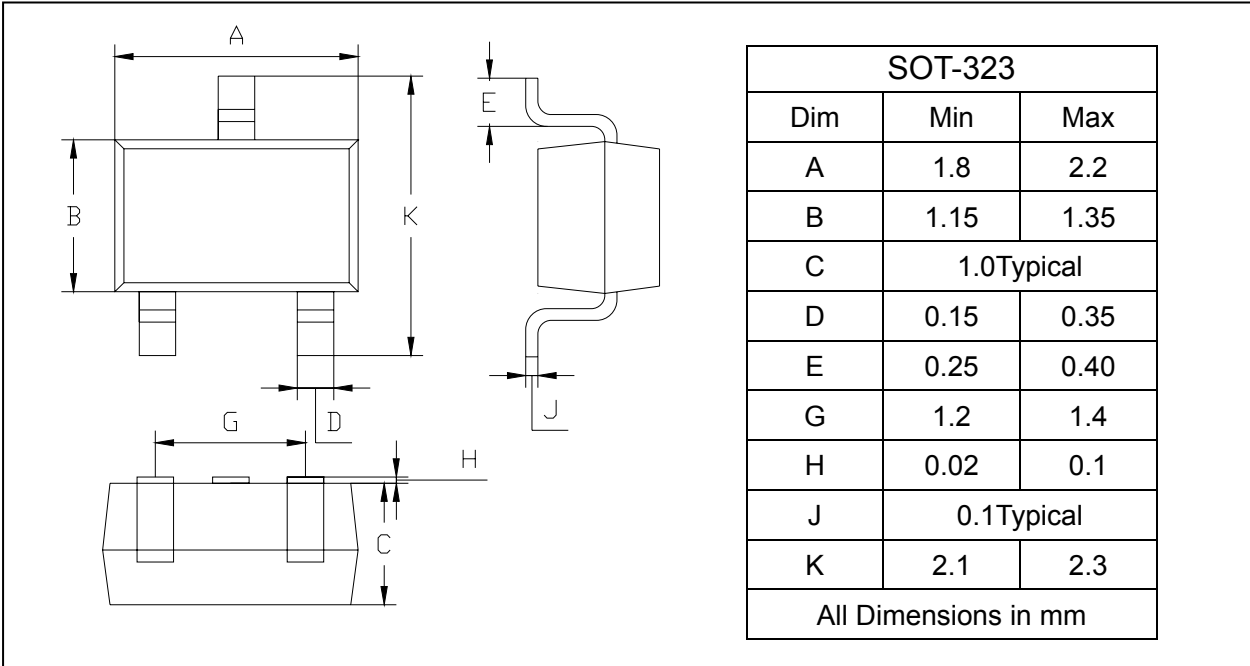
## PNP General Purpose Transistor

## MMST5401

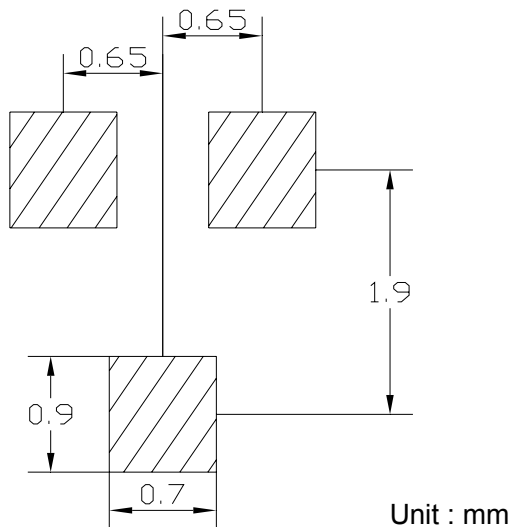
### PACKAGE OUTLINE

Plastic surface mounted package

SOT-323



### SOLDERING FOOTPRINT



### PACKAGE INFORMATION

| Device   | Package | Shipping       |
|----------|---------|----------------|
| MMST5401 | SOT-323 | 3000/Tape&Reel |

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